

ABSTRACT

There is provided is a technique including: a process chamber configured to process a substrate; a first gas supplier configured to supply a metal-containing gas into the process chamber; a second gas supplier configured to supply a first oxygen-containing gas from an interior of the process chamber; and an exhauster configured to discharge an exhaust gas containing a component of the metal-containing gas from the interior of the process chamber, wherein the exhauster includes a gas exhaust pipe, a pump configured to exhaust the interior of the process chamber, an auxiliary pump configured to support the pump, and a trap disposed between the pump and the auxiliary pump and configured to collect the component of the metal-containing gas by using plasma.

FIG. 1